# Assignment 1 & 2 Course 10401



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January 17, 2019

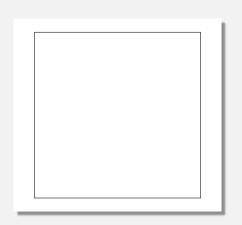
#### Introduction

L. R. Alcala-Jimenez, T. Passer, A. Lei, and E. V. Thomsen

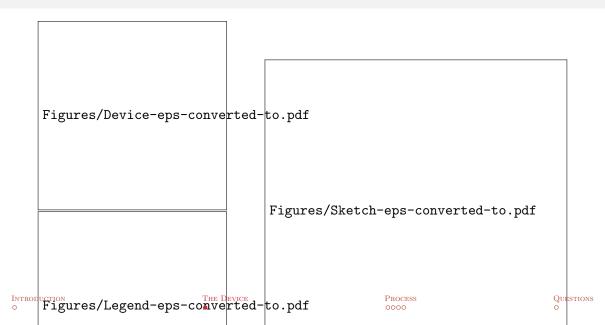
"Increased Mechanical Robustness of Piezoelectric Magnetoelastic Vibrational Energy Harvesters"

**43rd** International conference on Micro and Nano Engineering, (2017)

"This study presents a fabrication process for a mechanically robust piezo electric cantilever-based VEH suitable for magnetoelastic energy harvesting."



# PIEZOELECTRIC MAGNETOELASTIC VIBRATIONAL ENERGY HARVESTER



#### Growth and Mask

SUBSTRATE WAFER 350 µm, DSP,  $5.08\times 10^{19}\,\text{cm}^{-3}$ phosphorus doped,  $\{100\}$  oriented silicon wafer

**CLEANING RCA clean** 

3000 nm

WET OXIDE GROWTH 12 h 55 min @ 1150 °C:

INTROLITHOGRAPHY MASK 1.50 pm AZ: 4562 positive resist

Figures/Subs-eps-converted-to.pd:

### GROOVE AND ROUNDING CORNERS

SILICON ETCH 20% KOH @ 80°C for 3 h 36 min: 54.7° 310 µm groove

BHF OXIDE ETCH 45 min @ 70 nm/min

CLEANING RCA clean

THE DEVICE

WET OXIDE GROWTH 126 min @ 1100 °C:

Process Question

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Figures/KOH-eps-converted-to.pdf

#### Deposit and Liftoff

Figures/Deposit-eps-converted-to.pdf

Introduction The Device  $^{\circ}\Gamma_{I}/P_{T}$  Sputtering  $39\,W/cm^{\circ}$  at  $10\,cm$ 



## BEAM RELEASE AND FOILING

LITHOGRAPHY 5 µm AZ 4562 positive resist DRY SILICON ETHC STS ICP Advanced Silicon Etcher system. Vertical

Electrostatic tape holds

the wafer still. Removed

Figures/Cantirelease-eps-converted-t

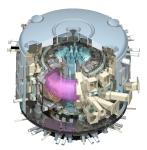
etch at 3000 nm/min for silicon.

DICING Disco DAD321.

Introduction

Process Question o

### QUESTIONS



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